

Superconducting MgB₂ Thin Films with $T_c \approx 39\text{K}$ Grown by Pulsed Laser Deposition

S.F.Wang, S.Y. Dai, Y..L.Zhou, Z.H.Chen, D.F.Cui, J.D.Yu, M.He, H.B.Lu, and G.Z.Yang

Laboratory of Optical Physics, Institute of Physics and Center for Condensed Mater Physcis, Chinese Academy of Sciences,

Beijing 100080, Peapoles Repulic of China

Superconducting MgB₂ thin films were fabricated on Al₂O₃(0001) substrates under an ex-situ processing conditions. Boron thin films were deposited by pulsed laser deposition followed by a post-annealing process. Resistance measurements of the deposited MgB₂ films show T_c of $\sim 39\text{K}$, while scanning electron microscopy and x-ray diffraction analysis indicate that the films consist of well-crystallized grains with a highly c-axis-oriented structure.

The discovery of superconductivity in MgB₂ with $T_c \approx 39\text{K}$ by Akimistu and coworkers^[1,2] offers a new class of simple, low-cost and high-performance binary intermetallic superconductors with a record high superconducting transition temperature for a nonoxide and non-*C60*-based compound. A significant experimental effort has been focused on the growth of MgB₂ films^[3-7] for the availability of such a film can be of great value for further basic studies and electronic applications. However, the growth of MgB₂ is complicated due to the large differences in vapor pressure between boron and magnesium and the high sensitivity of magnesium to oxidation. To overcome this two complicated factors for the fabrication of MgB₂ thin films, an ex-situ method is exploited, which are based on a similar approach as used in MgB₂ wires:^[8] magnesium atoms diffuse into boron films at high temperature and

high magnesium pressure.

In this paper, we report our results on the growth of MgB₂ thin films by an ex-situ method. First, boron films were deposited on Al₂O₃(0001) substrates at 900°C under the back ground pressure of 6×10^{-4} Pa by pulsed laser deposition. During deposition, an XeCl excimer-laser beam at a wavelength of 308nm was focused on the surface of the boron target. The laser spot sizes on the target were about 1.5mm² and the energy density at the target surface was 10J/cm². The laser was operated at 6Hz. Approximately 350--400nm thick boron films were prepared with a deposition rate of about 1Å/s. After deposition, the boron films were dipped into the high pure alcohol for 30min to get rid of the B₂O₃. Then the films together with magnesium and MgB₂ pellets, which were wrapped with tantalum foil, were annealed in an evacuated quartz tube at 900°C for 60min, after that, the samples were allowed to cool slowly to room temperature. The resistance measurement was performed with a standard four-probe technique. Scanning electron microscopy (SEM) and x-ray diffraction (XRD) were used to studied the properties of the MgB₂ films.

Figure 1 shows the temperature dependence of the resistance of MgB₂ thin films under zero magnetic field, the onset and zero-resistance temperatures are about 39K and 36K, respectively. A very sharp transition with a width of about 0.8K from 90% to 10% of the normal state resistance is observed, which is comparable to most of the high-quality bulk MgB₂ samples.

Fig.1 Resistance versus temperature for MgB₂ thin films on Al₂O₃(0001) substrates.

The surface morphology of the MgB₂ films grown on Al₂O₃(0001) substrates is

shown in Fig.2, well-defined, large hexagonal grains(1-2 μ m) and a porous appearance are observed in the magnified view of Fig. 2. X-ray energy dispersive spectroscopy (EDX) analysis shows only a small amount of oxygen contamination(0.3%) in the deposited MgB₂ films.

Fig.2 SEM image of the MgB₂ thin film with T_c ~ 39K on Al₂O₃(0001) substrates. The left one is a magnified view.

Figure 3 presents a typical x-ray diffraction pattern for the MgB₂ films grown on Al₂O₃(0001) substrates. Two sharp peaks corresponding to the MgB₂ (001) and (002) line indicates that most grains in the film have their *c*-axis orientation, the other two small peaks correspond to the remnant of Mg(101) and MgO(222) lines, which may be a possible explanation for lower transition temperature of MgB₂ thin films when compared to its bulk materials.

Fig.3 XRD patterns of the MgB₂ thin film with T_c ~ 39K on Al₂O₃(0001) substrates.

In summary, thin films of MgB₂ with T_c ~ 39K have been fabricated on Al₂O₃(0001) substrates. The deposition method was a two-step ex-situ approach. A deposition of boron films by pulsed laser deposition followed by a high magnesium pressure anneal step at 900 $^{\circ}$ C. The technique results a small amount of oxygen contamination, well-crystallized MgB₂ thin films with a highly *c*-axis-oriented structure.

References:

- [1] Akimitsu J, presentation at ‘ Symposium on Transition Metal Oxides’, Sendai,
January 10,2001
- [2] Nagamatsu J, Nakagawa N, Muranaka T et al 2001 Nature **410** 63
- [3] W.N.Kang, H.-J.Kiu, E.-M.Choi, et al 2001 Cond-mat/0103179
- [4] Eom C B, Lee M K, J.H.Choi,et al 2001 Cond-mat/0103425
- [5] H.M.Christen, H.Y.Zhai, C.Cantoni, etal, Submitted to Physica C(March 22, 2001)
- [6] A.Brinkman, D.Mijatoric, G.Rijnders, etal, Cond-mat/0103198(2001)
- [7] M.Paranthaman, C.Cantoni, H.Y.Zhai, etal, Cond-mat/0103569(2001)(submitted to
Appl.Phys.Lett.)
- [8] P.C.Canfield, D.K.Finnemore, S.L.Bud’ ko, etal, Phys.Rev.Lett. 86(2001)2423

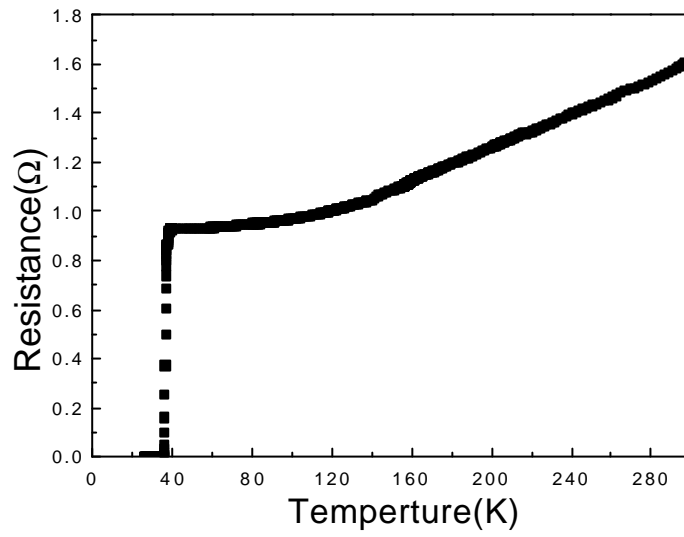


Fig.1 Resistance versus temperature for MgB_2 thin films on $\text{Al}_2\text{O}_3(0001)$ substrates.

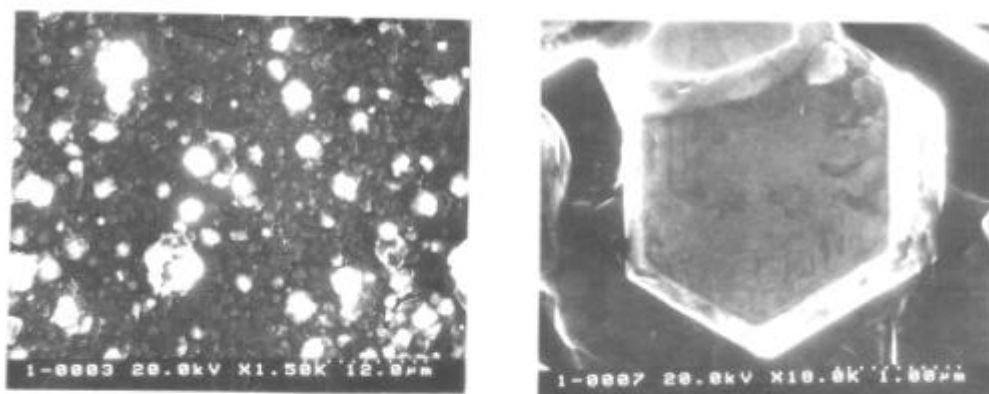


Fig.2 SEM image of the MgB_2 thin films with $T_c \sim 39\text{k}$ on $\text{Al}_2\text{O}_3(0001)$ substrates. The left one is a magnified view.

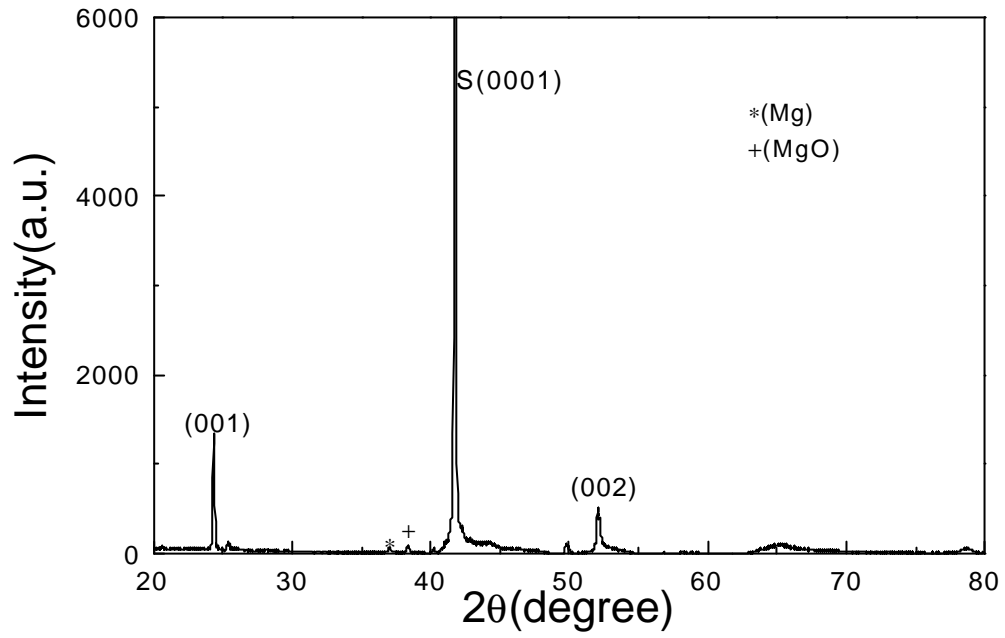


Fig.3 XRD patterns of the MgB_2 thin film with $T_c \sim 39\text{k}$ on $\text{Al}_2\text{O}_3(0001)$ substrates.